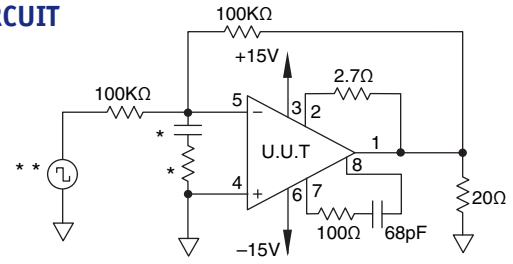
SG	PARAMETER***	SYMBOL	TEMP.	POWER	TEST CONDITIONS	MIN	MAX	UNITS
1	Quiescent current	I_Q	25°C	±150V	V_{IN} = 0, A_V = 100		25	mA
1	Input offset voltage	V_{OS}	25°C	±15V	V_{IN} = 0, A_V = 100		±4	mV
1	Input offset voltage	V_{OS}	25°C	±150V	V_{IN} = 0, A_V = 100		±2	mV
1	Input bias current, +IN	$+I_B$	25°C	±150V	V_{IN} = 0		±50	pA
1	Input bias current, –IN	$–I_B$	25°C	±150V	V_{IN} = 0		±50	pA
1	Input offset current	I_{OS}	25°C	±150V	V_{IN} = 0		±100	pA
3	Quiescent current	I_Q	–55°C	±150V	V_{IN} = 0, A_V = 100		28	mA
3	Input offset voltage	V_{OS}	–55°C	±15V	V_{IN} = 0, A_V = 100		±6.4	mV
3	Input offset voltage	V_{OS}	–55°C	±150V	V_{IN} = 0, A_V = 100		±4.4	mV
3	Input bias current, +IN	$+I_B$	–55°C	±150V	V_{IN} = 0		±50	pA
3	Input bias current, –IN	$–I_B$	–55°C	±150V	V_{IN} = 0		±50	pA
3	Input offset current	I_{OS}	–55°C	±150V	V_{IN} = 0		±50	pA
2	Quiescent current	I_Q	125°C	±150V	V_{IN} = 0, A_V = 100		28	mA
2	Input offset voltage	V_{OS}	125°C	±15V	V_{IN} = 0, A_V = 100		±7	mV
2	Input offset voltage	V_{OS}	125°C	±150V	V_{IN} = 0, A_V = 100		±5	mV
2	Input bias current, +IN	$+I_B$	125°C	±150V	V_{IN} = 0		±10	nA
2	Input bias current, –IN	$–I_B$	125°C	±150V	V_{IN} = 0		±10	nA
2	Input offset current	I_{OS}	125°C	±150V	V_{IN} = 0		±10	nA
4	Output voltage, I_O = 200mA	V_O	25°C	±50V	R_L = 200Ω	40		V
4	Output voltage, I_O = 70mA	V_O	25°C	±150V	R_L = 2KΩ	141		V
4	Output voltage, I_O = 20mA	V_O	25°C	±48V	R_L = 2KΩ	40		V
4	Current limits	I_{CL}	25°C	±50V	R_{CL} = 10Ω, R_L = 200Ω	60	112	mA
4	Stability/noise	E_N	25°C	±150V	C_C = 68pF, R_C = 100Ω, A_V = +1, C_L = 470pF		1	mV
4	Slew rate	SR	25°C	±150V	R_L = 2KΩ, A_V = 100, C_C = OPEN	400		V/µs
4	Open loop gain	A_{OL}	25°C	±150V	R_L = 2KΩ, F = 15Hz, C_C = OPEN	96		dB
4	Common-mode rejection	CMR	25°C	±150V	F = DC, V_{CM} = ±90V	90		dB
6	Output voltage, I_O = 200mA	V_O	–55°C	±50V	R_L = 200Ω	40		V
6	Output voltage, I_O = 70mA	V_O	–55°C	±150V	R_L = 2KΩ	141		V
6	Output voltage, I_O = 20mA	V_O	–55°C	±48V	R_L = 2KΩ	40		V
6	Stability/noise	E_N	–55°C	±150V	C_C = 68pF, R_C = 100Ω, A_V = +1, C_L = 470pF		1	mV
6	Slew rate	SR	–55°C	±150V	R_L = 2KΩ, A_V = 100, C_C = OPEN	400		V/µs
6	Open loop gain	A_{OL}	–55°C	±150V	R_L = 2KΩ, F = 15Hz, C_C = OPEN	96		dB
6	Common-mode rejection	CMR	–55°C	±150V	F = DC, V_{CM} = ±90V	90		dB
5	Output voltage, I_O = 150mA	V_O	125°C	±40V	R_L = 200Ω	30		V
5	Output voltage, I_O = 70mA	V_O	125°C	±150V	R_L = 2KΩ	141		V
5	Output voltage, I_O = 20mA	V_O	125°C	±48V	R_L = 2KΩ	40		V
5	Stability/noise	E_N	125°C	±150V	C_C = 68pF, R_C = 100Ω, A_V = +1, C_L = 470pF		1	mV
5	Slew rate	SR	125°C	±150V	R_L = 2KΩ, A_V = 100, C_C = OPEN	400		V/µs
5	Open loop gain	A_{OL}	125°C	±150V	R_L = 2KΩ, F = 15Hz, C_C = OPEN	96		dB
5	Common-mode rejection	CMR	125°C	±150V	F = DC, V_{CM} = ±90V	90		dB

BURN IN CIRCUIT



* These components are used to stabilize device due to poor high frequency characteristics of burn in board.

** Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C.

*** An additional test is performed manually at T_C = 25°C which stresses power supply, common mode range and output swing to ±225V (450V total).